

CNES-ESA Radiation Final Presentation Days, 09-10 march 2015

SESSION

RADIATION EFFECTS ON OPTOELECTRONICS

Chairmans

Mathieu BOUTILLIER
Olivier GILARD

OUTLINE

14:00		Radiation effects on optoelectronics		
14:00	20m	Cryogenic radiations facility (80K): validation of CNES cryostat on UCL HIF facility	M. Boutillier B. Baradat	CNES
14:20	20m	Single Event Upset Sensitivity of D-Latch in Infrared Image Sensors for Low Temperature Applications	L. Artola	ONERA
14:40	20m	Low temperature total dose irradiation of different transistor topologies for infrared applications	T. Nuns	ONERA
15:00	20m	Commercial Light Emitting Diodes sensitivity to protons radiations	M. Boutillier	CNES
15:20	20m	Radiation effects on digital CMOS image sensors using micro lenses and color filters	A. Toulemon	CNES